

# LDMOS AND CMOS INTEGRATED CIRCUIT AND METHOD OF MAKING

5

## **ABSTRACT OF THE DISCLOSURE**

An integrated circuit (IC) is formed on a substrate. The IC has a first well having a first dopant concentration that includes a second conductivity low-voltage transistor. The IC also has a second well having a dopant concentration equal to the first dopant concentration that includes a first conductivity high-voltage transistor. In addition, the IC has a third well having a second dopant concentration of an opposite type than the first well that includes a first conductivity low-voltage transistor. The first conductivity low-voltage transistor and the second conductivity low-voltage transistor are created without a threshold voltage ( $V_t$ ) implant.

15